



## **OVERVOLTAGE PROTECTION CONTROLLER**

### FEATURES

- Up to 100-V Overvoltage Protection
- 6.9-V Overvoltage Shutdown Threshold
- 3.0-V Undervoltage Shutdown Threshold
- Overvoltage Turn-Off Time Less than 1.0 μs
- External N-Channel MOSFET Driven by Internal Charge Pump
- 1-mA Maximum Static Supply Current
- 5-Pin SOT-23 Package
- -40°C to 85°C Ambient Temperature Range
- 2.5-kV Human-Body-Model, 500-V CDM Electrostatic Discharge Protection

### APPLICATIONS

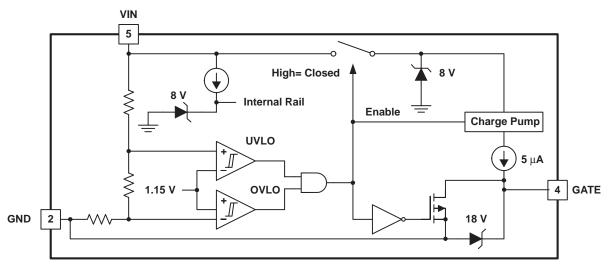
- Cellular Phones
- PDAs
- Portable PCs
- Media Players
- Digital Cameras
- GPS

### FUNCTIONAL BLOCK DIAGRAM

### DESCRIPTION

The TPS2400 overvoltage protection controller is used with an external N-channel MOSFET to isolate sensitive electronics from destructive voltage spikes and surges. It is specifically designed to prevent large voltage transients associated with automotive environments (load dump) from damaging sensitive circuitry. When potentially damaging voltage levels are detected by the TPS2400 the supply is disconnected from the load before any damage can occur.

Internal circuitry includes a trimmed band-gap reference, oscillator, zener diode, charge pump, comparator, and control logic. The TPS2400 is designed for use with an external N-channel MOSFET which are readily available in a wide variety of voltages.



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## **TPS2400**

#### SLUS599A - JUNE 2004 - REVISED AUGUST 2008



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		TPS2400	UNIT
Input voltage range, VIN	VIN	-0.3 to 110	
	GATE (continuous)	-0.3 to 22	V
Output voltage range, V <sub>OUT</sub>	GATE (transient, < 10 µs, Duty Cycle < 0.1%)	-0.3 to 25	
Continuous total power dissipation	See dissipation ra	ting table	
Operating junction temperature range, TJ	-40 to 125		
Operating free-air temperature range, TA	-40 to 85		
Storage temperature range, Tstg	-65 to 150	°C	
Lead temperature soldering 1, 6 mm (1/16 inch	260		

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. All voltages are with respect to GND.

## **DISSIPATION RATINGS**

PACKAGE	T <sub>A</sub> < 25°C	DERATING FACTOR T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING
SOT-23	285 mW	2.85 mW/°C	155 mW	114 mW

### **RECOMMENDED OPERATING CONDITIONS**

	MIN	NOM	MAX	UNIT
Supply voltage at V <sub>IN</sub>	3.1		6.8	V
Operating junction temperature	-40		125	°C

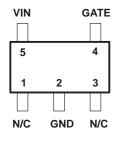
## **ELECTROSTATIC DISCHARGE (ESD) PROTECTION**

	MIN	MAX	UNIT
Human Body Model	2.5		1.57
CDM	0.5		kV

### **ORDERING INFORMATION**

$T_A = T_J$	PACKAGED DEVICES SOT23–5 (DBV)	QUANTITY PER REEL		
–40°C to 85°C	TPS2400DBVR	3000		
	TPS2400DBVT	500		







### **ELECTRICAL CHARACTERISTICS**

 $T_A = -40^\circ C$  to  $85^\circ C,\, T_J = -40^\circ C$  to  $125^\circ C$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT		·				•
		V <sub>I(VIN)</sub> = 3.1 V		65	110	
		$V_{I(VIN)} = 5.0 V$		95	180	
II(VIN)	Input supply current, VIN	V <sub>I(VIN)</sub> = 6.5 V		135	220	μA
		V <sub>I(VIN)</sub> = 100 V		550	1000	
UVLO <sub>(upper)</sub>	Undervoltage lockout upper threshold	VI(VIN) rising	2.9	3.0	3.1	V
UVLO <sub>(hyst)</sub>	Undervoltage lockout hysteresis		85	100	115	mV
OVP <sub>(upper)</sub>	Overvoltage protection upper threshold	V <sub>I(VIN)</sub> rising	6.7	6.9	7.1	V
OVP(hyst)	Overvoltage protection hysteresis		135	150	165	mV
GATE DRIVE						
		V <sub>I(VIN)</sub> = 3.1 V, V <sub>O(gate)</sub> = 7 V			10	
IOSOURCE(gate)	Gate sourcing current	V <sub>I(VIN)</sub> = 5 V, V <sub>O(gate)</sub> = 10 V	3		10	μA
IOSINK(gate)	Gate sinking current <sup>(1)</sup>	V <sub>I(VIN)</sub> = 7.2 V, V <sub>O(gate)</sub> = 15 V	350	485	600	mA
		V <sub>I(VIN)</sub> =3.1 V, IOSOURCE(gate)=1.0 µA	10		12	
VOH(gate)	Gate output high voltage	VI(VIN) = 5 V, IOSOURCE(gate) = 1.5 µA	16		19	
		VI(VIN) = 6.5 V, IOSOURCE(gate) = 1.5 µA	16		20	V
VOHMAX(gate)	Gate output high maximum voltage	IOSOURCE(gate) = 0 µA			20	
VOL(gate)	Gate output low voltage	VI(VIN) = 7.2 V, IOSINK(gate) = 50 mA			1.0	
TON(prop)	Gate turn-on propogation delay, (50%	$V_{I(VIN)}$ stepped from 0 V to 5 V, $C_{LOAD} = 1 \text{ nF}$	0.1		0.6	
(	$V_{I(vin)}$ to $V_{O(gate)} = 1 V$ , $R_{LOAD} = 10 M\Omega$ )	C <sub>LOAD</sub> = 10 nF	0.9		3	
T <sub>ON(rise)</sub>	Gate turn-on rise time, $(V_O(gate)) = 1 \vee to$	$V_{I(VIN)}$ stepped from 0 V to 5V, $C_{LOAD} = 1 \text{ nF}$	1.5		6	ms
	90% VO(gate) , $R_{LOAD}$ = 10 M $\Omega$ )	C <sub>LOAD</sub> = 10 nF	15 55			
TOFF	Turn-off time, (50% $V_{I(VIN)}$ step to	V <sub>I(VIN)</sub> stepped from 6 V to 8 V, C <sub>LOAD</sub> = 1 nF			0.25	μs
	$V_{O}(GATE) = 6.9 \text{ V}, \text{ R}_{LOAD} = 10 \text{ meg } \Omega$ )	$C_{LOAD} = 10 \text{ nF}$			0.5	

(1) Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.



#### TERMINAL FUNCTIONS

Term	ninals						
Name	No.	I/O	Description				
GATE	4	0	Output gate drive for an external N-channel MOSFET.				
GND	2	-	Ground				
NC	1	-					
NC	3	-	No internal connection				
VIN	5	Ι	Input voltage				

### DETAILED DESCRIPTION

#### Undervoltage and Overvoltage Comparators and Logic

When the comparators detect that  $V_{CC}$  is within the operating window, the GATE output is driven high to turn on the external N-channel MOSFET. When  $V_{CC}$  goes above the set overvoltage level, or below the set undervoltage level, the GATE output is driven low.

#### Charge pump

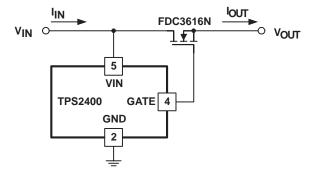
An internal charge pump supplies power to the GATE drive circuit and provides the necessary voltage to pull the gate of the MOSFET above the source.

#### Zener Diodes

Limit internal power rails to 8.0 V and GATE output to 18 V.

#### Shut-Off MOSFET

When an undervoltage or overvoltage event occurs, this MOSFET is turned on to pull down the gate of the external N-channel MOSFET, thus isolating the load from the incoming transient.



UDG-04056

**Figure 1. Application Diagram** 



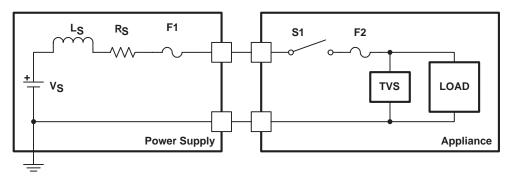
## **APPLICATION INFORMATION**

#### **Overvoltage Protection**

An overvoltage condition is commonly created in these situations.

- Unplugging a wall adapter from an AC outlet. Energy stored in the transformer magnetizing inductance is released and spikes the output voltage.
- Powering an appliance with the wrong voltage adapter (user error)
- Automotive load dump due to ignition, power windows, or starter motor (for example)
- An AC power-line transient
- Power switch contact bounce (causes power supply/distribution inductive kick), (See Figure 2)

Many electronic appliances use a transient voltage suppressor (TVS) for overvoltage protection as shown in Figure 2. The TVS is typically a metal-oxide varister (MOV) or Transzorb. The former is a non-linear resistor with a soft turn-on characteristic whereas the latter is a large junction zener diode with a very sharp turn-on characteristic. These devices have high pulse-power capability and pico-second response time. A TVS clamps the load voltage to a safe level so the load operates uninterrupted in the presence of power supply output-voltage spikes. But in the event of a voltage surge, fuse F2 blows and must be replaced to restore operation.



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Figure 2. Load Protection Using Transient Voltage Suppressor Clamps

The TPS2400 circuit in Figure 3 protects the load from an overvoltage, not by clamping the load voltage like a TVS, but by disconnecting the load from the power supply. The circuit responds to an overvoltage in less than 1  $\mu$ s and rides out a voltage surge without blowing fuse F2. Note that the voltage surge can be of indefinite duration.

The load can see a voltage spike of up to 1  $\mu$ s, the amount of time it takes the TPS2400 to disconnect the load from the power supply. A low-power zener diode D2 can be used to clamp the load voltage to a safe level. In most cases, diode D2 is not necessary since the load bypass capacitor (not shown) forms a low-pass filter with resistor R<sub>S</sub> and inductor L<sub>S</sub> to significantly attenuate the spike.



## **APPLICATION INFORMATION**

When the TPS2400 disconnects the load from the power supply, the power-supply output-voltage spikes as the stored energy in inductor  $L_S$  is released. A zener diode D1 or a small ceramic capacitor can be used to keep the voltage spike at a safe level.

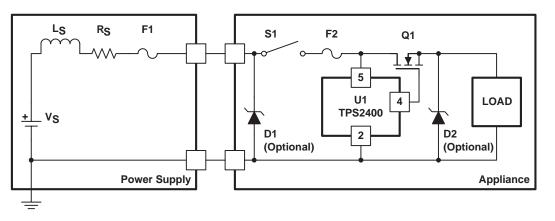


Figure 3. TPS2400 Application Block Diagram

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#### **Controlling the Load Inrush-Current**

Figure 4 is a simplified representation of an appliance with a plug-in power supply (e.g., wall adapter). When power is first applied to the load in Figure 4, the large filter capacitor  $C_{LOAD}$  acts like a short circuit, producing an immediate inrush-current that is limited by the power-supply output resistance and inductance,  $R_S$  and  $L_S$ , respectively. This current can be several orders of magnitude greater than the steady-state load current. The large inrush current can damage power connectors P1 and J1 and power switch S1, and stress components. Increasing the power-supply output resistance and inductance lowers the inrush current. However, the former increases system power-dissipation and the latter decreases connector and switch reliability by encouraging the contacts to arc when they bounce.

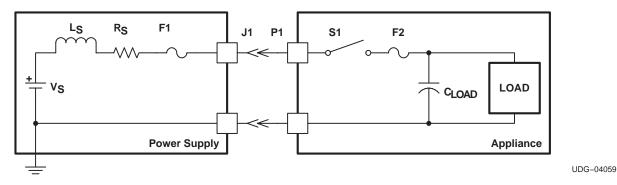


Figure 4. Power-Supply Output Resistance and Inductance Circuit Model



## **APPLICATION INFORMATION**

The TPS2400 circuit in Figure 5 limits the inrush current without these draw backs. The TPS2400 charges the transistor Q1 gate capacitance  $C_G$  with a 5- $\mu$ A source when Q1 is commanded to turn on. Transistor Q1 is wired as a source follower so the gate-voltage slew rate and the load-voltage slew rate are identical and equal to

$$\frac{\partial V_{L}}{\partial t} = \frac{5 \,\mu A}{C_{G}} \tag{1}$$

The corresponding inrush current is:

$$I_{\text{INRUSH}} \approx C_{\text{L}} \times \frac{\partial V_{\text{L}}}{\partial t} = \left(\frac{C_{\text{L}}}{C_{\text{G}}}\right) \times 5 \,\mu\text{A}$$
 (2)

An external capacitor and a series  $1-k\Omega$  resistor can be connected to the gate of Q1 and ground to reduce inrush current further. In this case, the parameter C<sub>G</sub> in equations 1 and 2 is the sum of the internal and external FET gate capacitance. The  $1-k\Omega$  resistor decouples the external gate capacitor so the TPS2400 can rapidly turn off transistor Q1 in response to an overvoltage condition.

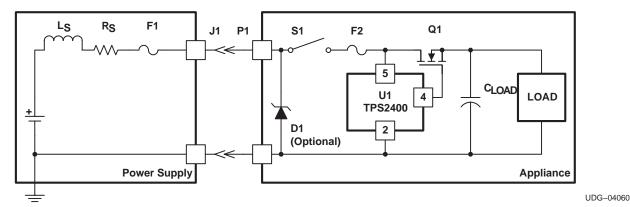
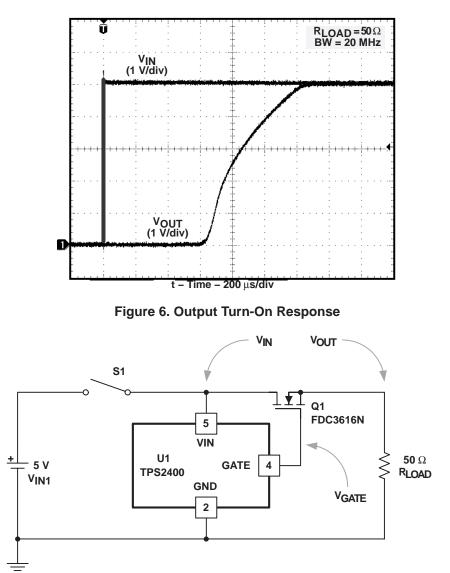


Figure 5. Turn-On Voltage Slew Rate Control Using the TPS2400

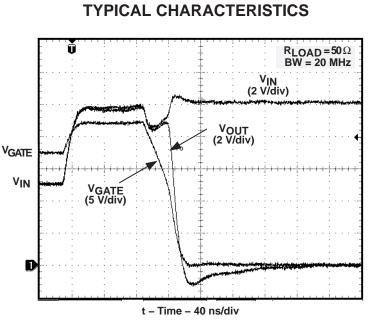




## **TYPICAL CHARACTERISTICS**

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## Figure 8. Output Turn-Off Response

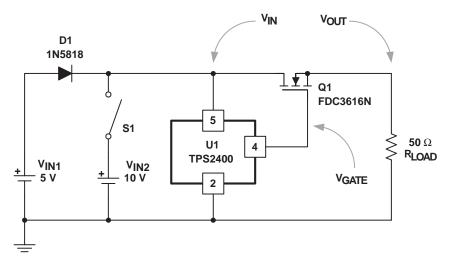


Figure 9. Output Turn-Off Response Test Circuit



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## **TPS2400**

### **APPLICATION INFORMATION**

### **Application Ideas**

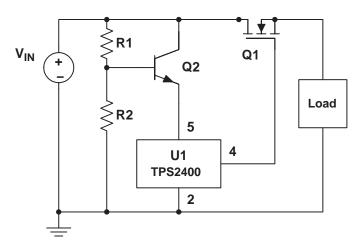


Figure 10. High–Side Switch Overvoltage protector that can drive a 12–V Load

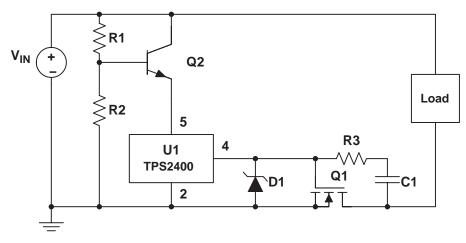
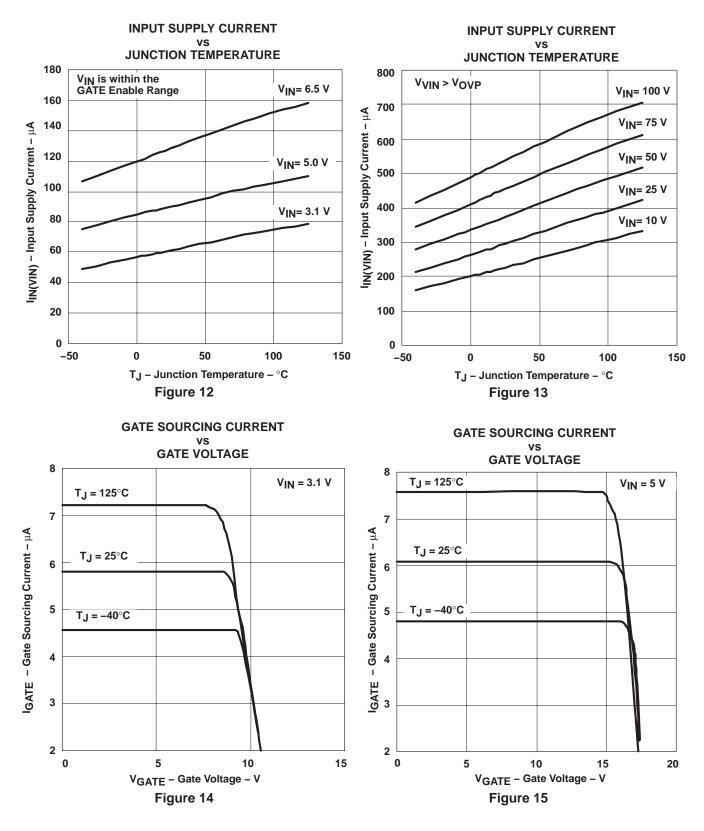


Figure 11. Low-Side Switch Overvoltage protector that can drive a 12-V Load

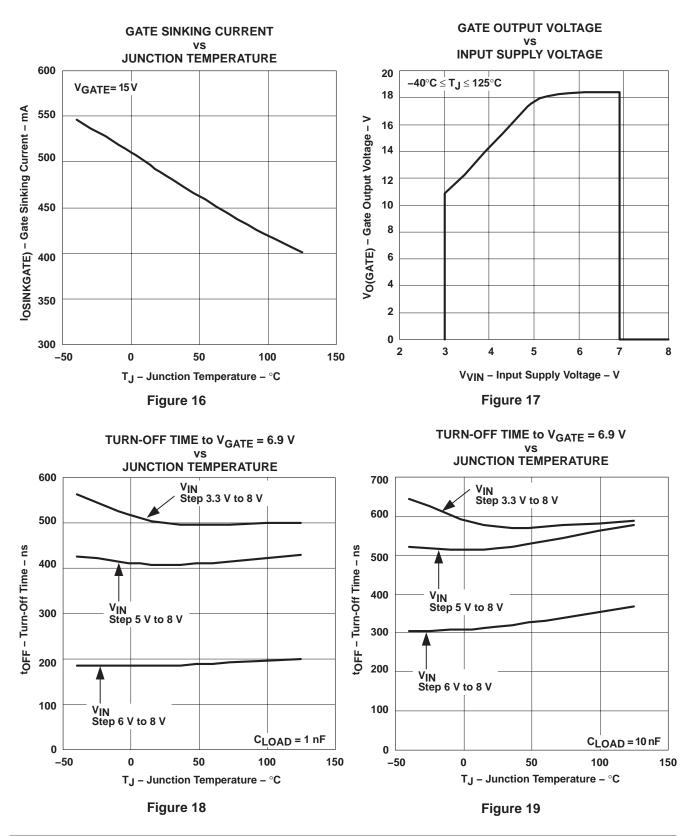
Refer to Texas Instrument's Application Note, *Overvoltage Protector for High–Voltage Loads* (TI Literature Number SLVA163 at www.ti.com) for more information.





### **TYPICAL CHARACTERISTICS**





## **TYPICAL CHARACTERISTICS**



#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPS2400DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS2400DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS2400DBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TPS2400DBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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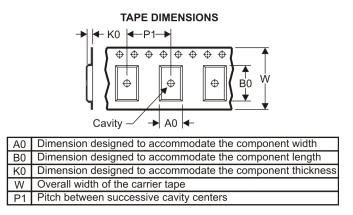
# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2400DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2400DBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

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# PACKAGE MATERIALS INFORMATION

4-May-2011



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2400DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TPS2400DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

D. Falls within JEDEC MO-178 Variation AA.



DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.

- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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